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(54) **MEMORY DEVICE AND METHOD FOR MANUFACTURING THE SAME USING HARD MASK**

(71) Applicant: **TAIWAN SEMICONDUCTOR MANUFACTURING COMPANY, LTD.**, Hsinchu (TW)

(72) Inventors: **Meng-Han LIN**, Hsinchu (TW); **Feng-Cheng YANG**, Hsinchu (TW)

(73) Assignee: **TAIWAN SEMICONDUCTOR MANUFACTURING COMPANY, LTD.**, Hsinchu (TW)

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(57) **ABSTRACT**

A semiconductor device includes an underlying substrate, two stack units disposed over the underlying substrate, and a feature disposed between the stack units. The stack units are spaced apart from each other. Each of the stack units includes a plurality of conductive films and a plurality of dielectric films disposed to alternate with the conductive films, an inter-metal dielectric (IMD) portion, and a hard mask film. An uppermost one of the dielectric films of each of the stack units is disposed over the conductive films, and has a dimension smaller than those of the conductive films and those of remaining ones of the dielectric films of each of the stack units. The feature includes a plurality of repeating units and a plurality of separators which are disposed to alternate with the repeating units. A method for manufacturing the semiconductor device is also disclosed.